

NVMFS6B75NL

Power MOSFET

100 V, 30 mΩ, 28 A, Single N-Channel

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS6B75NLWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	100	V
Gate-to-Source Voltage		V_{GS}	± 16	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)	Steady State	$T_C = 25^\circ\text{C}$	I_D	28
		$T_C = 100^\circ\text{C}$		19.7
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)		$T_C = 25^\circ\text{C}$	P_D	56
		$T_C = 100^\circ\text{C}$		28
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	7.0
		$T_A = 100^\circ\text{C}$		5.0
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)		$T_A = 25^\circ\text{C}$	P_D	3.5
		$T_A = 100^\circ\text{C}$		1.75
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10\ \mu\text{s}$	I_{DM}	141	A
Operating Junction and Storage Temperature		T_J , T_{stg}	-55 to +175	°C
Source Current (Body Diode)		I_S	43	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 1.7\text{ A}$)		E_{AS}	177	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	2.7	°C/W
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	43	

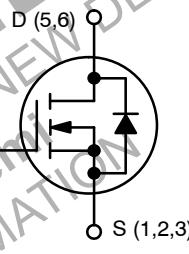
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

ON

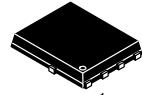
ON Semiconductor®

www.onsemi.com

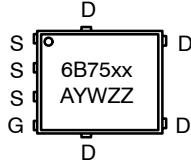
$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
100 V	30 mΩ @ 10 V	
	46 mΩ @ 4.5 V	28 A



N-CHANNEL MOSFET



1
DFN5
(SO-8FL)
CASE 488AA
STYLE 1



6B75NL = NVMFS6B75NL

6B75LW = NVMFS6B75NLWF

A = Assembly Location

Y = Year

W = Work Week

ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NVMFS6B75NL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA		100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				62		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 80 V	T _J = 25°C		10		μA
			T _J = 125°C			250	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 16 V				100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA		1.0		3.0	V
Threshold Temperature Coefficient	V _{GS(TH)} /T _J				-5.3		mV/°C
Drain-to-Source On Resistance	R _{DSS(on)}	V _{GS} = 10 V	I _D = 10 A		24.7	30	mΩ
		V _{GS} = 4.5 V			35	46	

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V		740		pF
Output Capacitance	C _{OSS}			260		
Reverse Transfer Capacitance	C _{rss}			20		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 50 V; I _D = 25 A		5.4		nC
				11.3		
				1.6		
		V _{GS} = 10 V, V _{DS} = 50 V; I _D = 25 A		3.2		
				1.5		
				3.8		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 50 V, I _D = 25 A, R _G = 2.5 Ω		9.1		ns
Rise Time	t _r			88.3		
Turn-Off Delay Time	t _{d(OFF)}			16		
Fall Time	t _f			71.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 20 A	T _J = 25°C		0.94	1.2	V
			T _J = 125°C		0.84		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 25 A			38.4		ns
Charge Time	t _a				22.6		
Discharge Time	t _b				15.8		
Reverse Recovery Charge	Q _{RR}				40		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

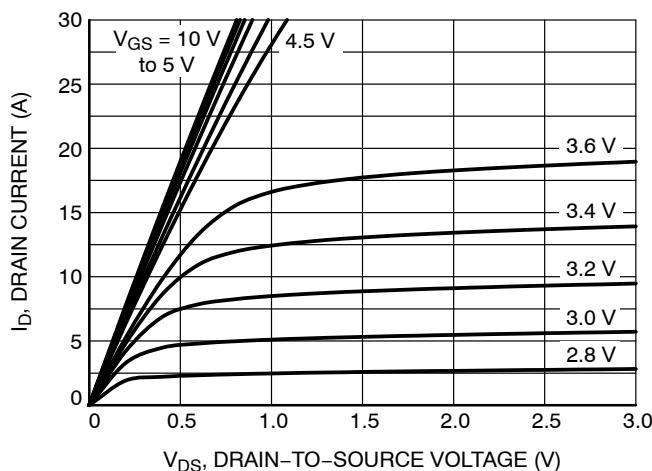


Figure 1. On-Region Characteristics

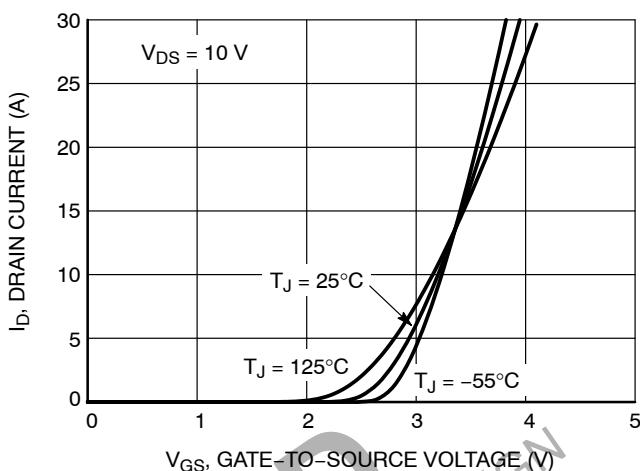


Figure 2. Transfer Characteristics

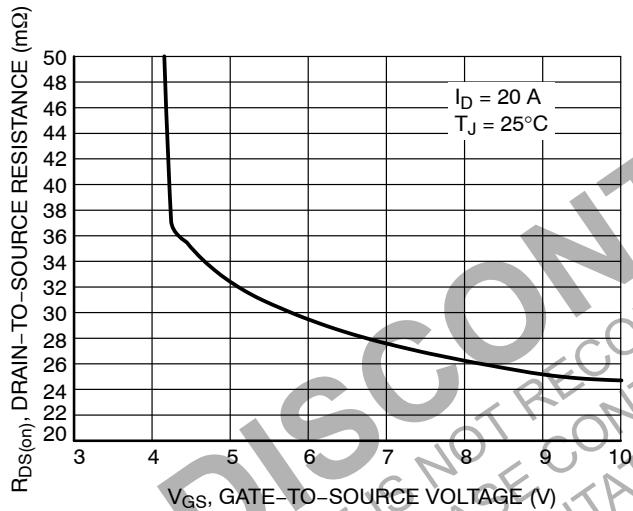


Figure 3. On-Resistance vs. Gate-to-Source Voltage

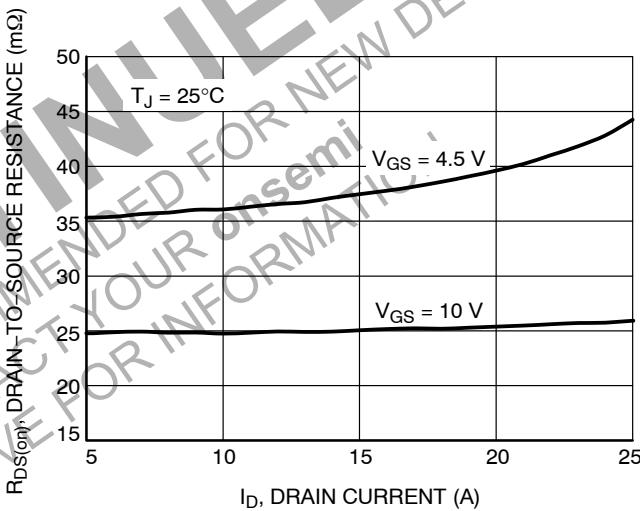


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

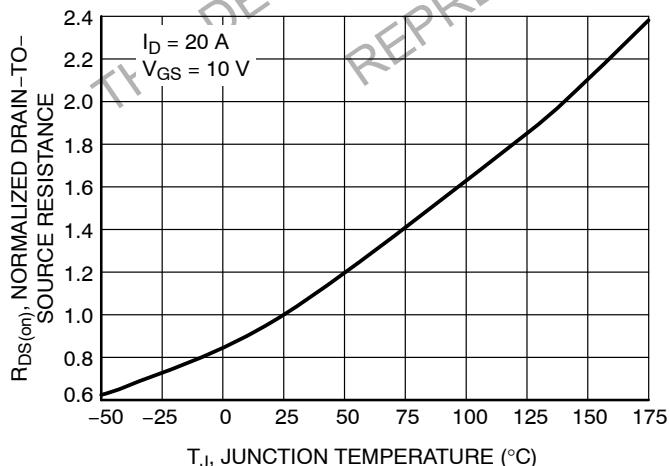


Figure 5. On-Resistance Variation with Temperature

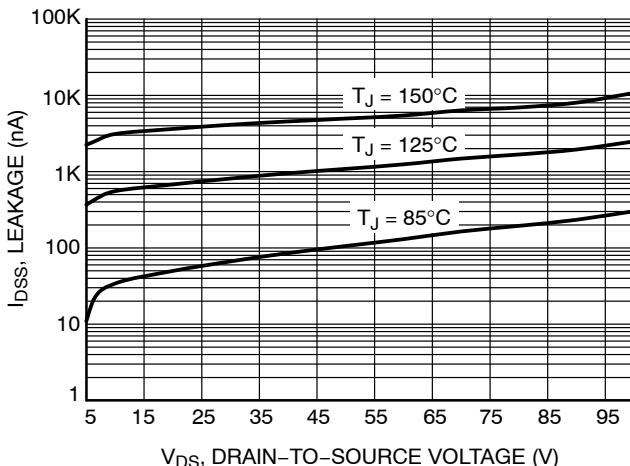


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

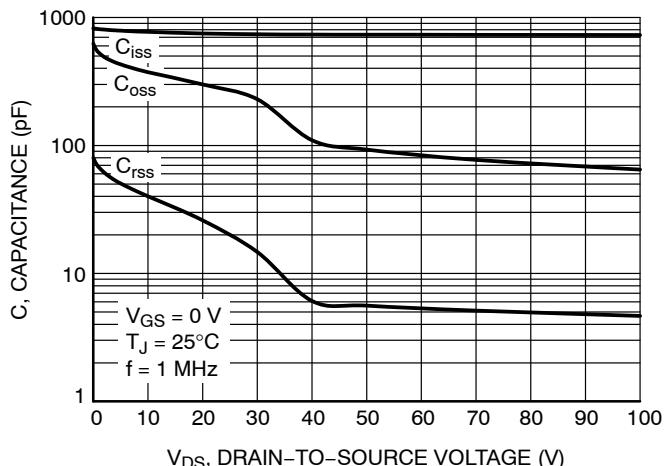


Figure 7. Capacitance Variation

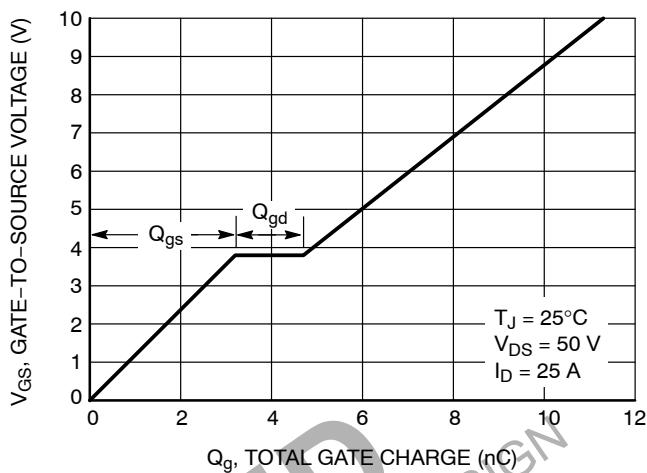


Figure 8. Gate-to-Source Voltage vs. Total Charge

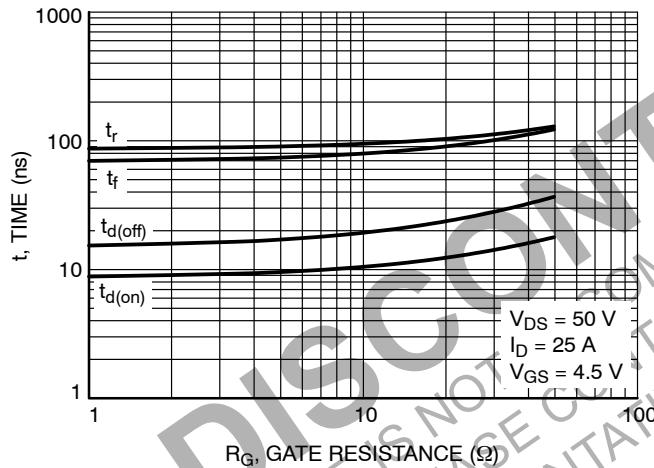


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

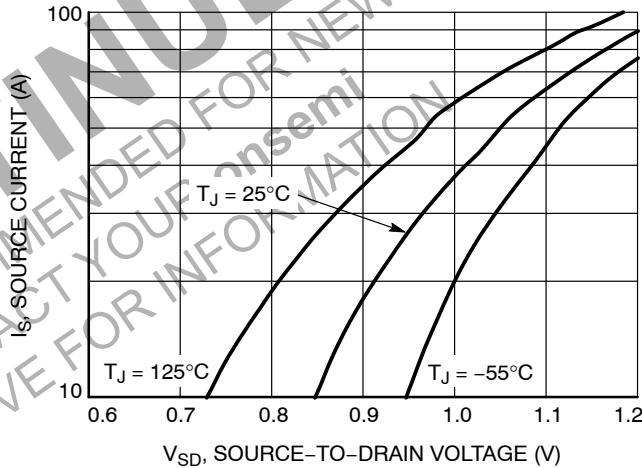


Figure 10. Diode Forward Voltage vs. Current

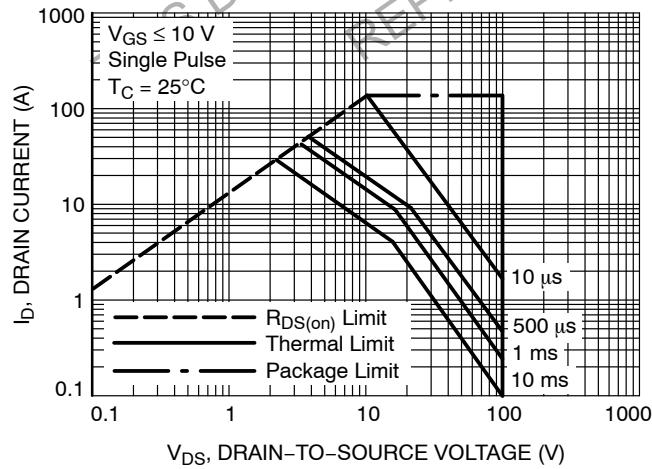
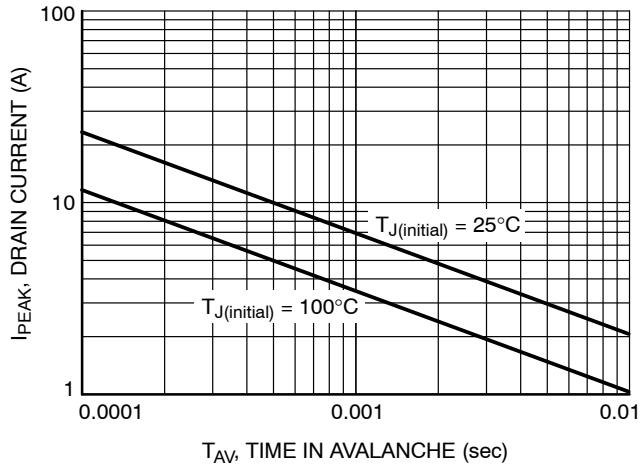


Figure 11. Maximum Rated Forward Biased Safe Operating Area

Figure 12. I_{PEAK} vs. T_{AV}

TYPICAL CHARACTERISTICS

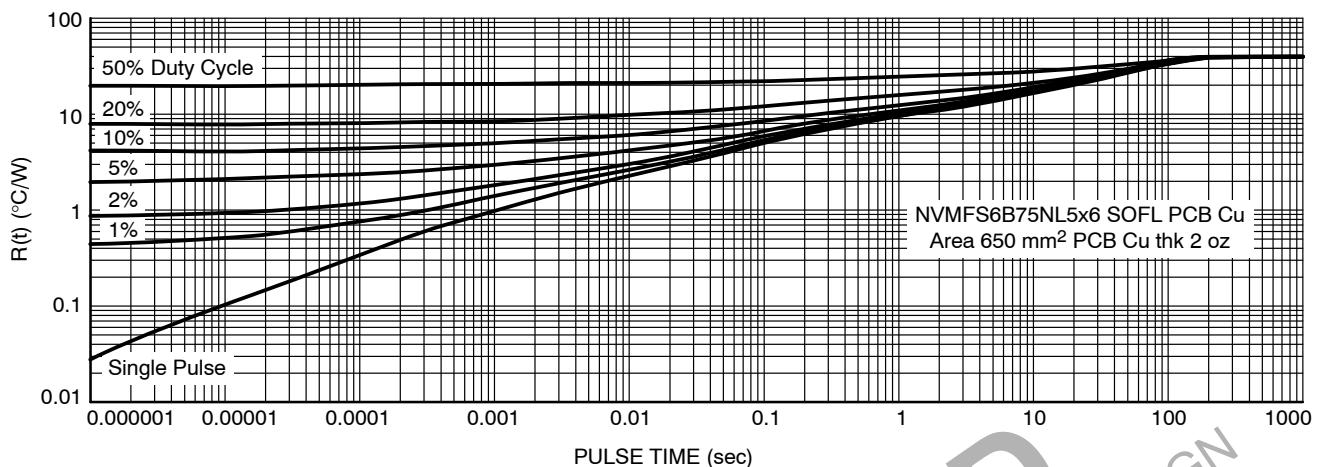
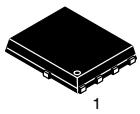


Figure 13. Thermal Response

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFS6B75NLT1G	6B75NL	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS6B75NLWFT1G	6B75LW	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel
NVMFS6B75NLT3G	6B75NL	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS6B75NLWFT3G	6B75LW	DFN5 (Pb-Free, Wettable Flanks)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SCALE 2:1

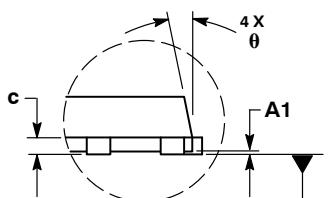
DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

NOTES:

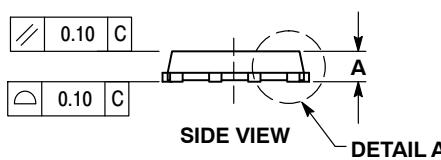
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	---	12 °

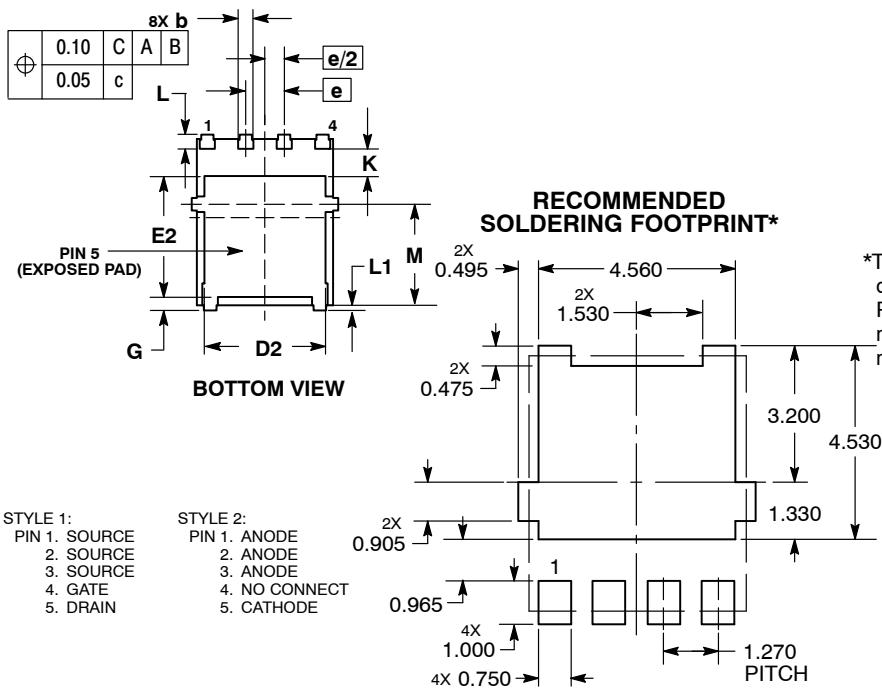


DETAIL A

SEATING PLANE



DETAIL A



STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

DIMENSIONS: MILLIMETERS

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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